

PHOTO TRANSISTOR

▼CHARACTERISTICS BY MATERIAL

Ta=25°C

Type No.	Absolute Maximum						Electro-Optical Characteristics							
	Collector Dissipation	Emitter-Collector Breakdown Voltage	Collector-Emitter Breakdown Voltage	Collector Current	Operating Temp.	Storage Temp.	Dark Current I _{ce0}		Dark Current Tr-Tf			Peak Sensitive Wavelength		
	Type	P _c	V _{CEO}	V _{CE0}	I _c	T _{opr}	T _{stg}	MAX.	V _{CEP}	TYP.	V _{CE}	I _c	R _L	λ _p TYP.
PS	TO-18	150	30	5	50	-30~+125	-30~+150	0.2	10	5	10	2	100	880
	502	60			20	-30~+85	-30~+100							
		100			30									
Units		mW	V	V	mA	°C	°C	μA	V	μsec	V	mA	Ω	nm

▼CHARACTERISTICS BY SHAPE

Ta=25°C

Shape	Type No.	Features	Peak Sensitive Wavelength λ _p TYP.	Photo Current I _c				Spatial Distribution (The typical distribution example of each shape is shown below)	Fig.
				MIN.	TYP.	V _{CE}	E _e		
	PS2022	TO-18 can type, flat lens	880	0.1	2.5	5	1		20
	PS3022	φ 5 molded epoxy type, high-directivity lens	880	1.5	7	5	1		21
	PS3322	φ 3 molded epoxy type, high-directivity lens	880	1.2	3.6	5	1		22
	PS3072	φ 3 molded epoxy type	880	0.2	0.7	5	1		23
	PS4032	φ 3 molded epoxy type, flat lens	880	1.5	5	5	10		24
	PS5022	φ 1.7 axial-lead type	880	0.4	2	5	1		25
	PS5042	φ 3.6 side-view type	880	0.4	1.4	5	1		26
	PS5052	side-view type high-directivity	880	0.3	1.4	5	1		27
Units			nm	mA		V	mW/cm ²		





▼ CHARACTERISTICS BY SHAPE

Ta=25°C

Shape	Type No.	Features	Peak Sensitive Wavelength λp TYP.	Photo Current Ic			Vce	Ea	Spatial Distribution (The typical shape distribution example of each shape is shown below)	fig.
				MIN.	TYP.	MAX.				
	PS1101W	Chip type	880	0.7	3.5	5	5		28	
Units			nm	mA		V	mW/cm ²			

▼ PACKAGE DIMENSIONS Unit : mm

